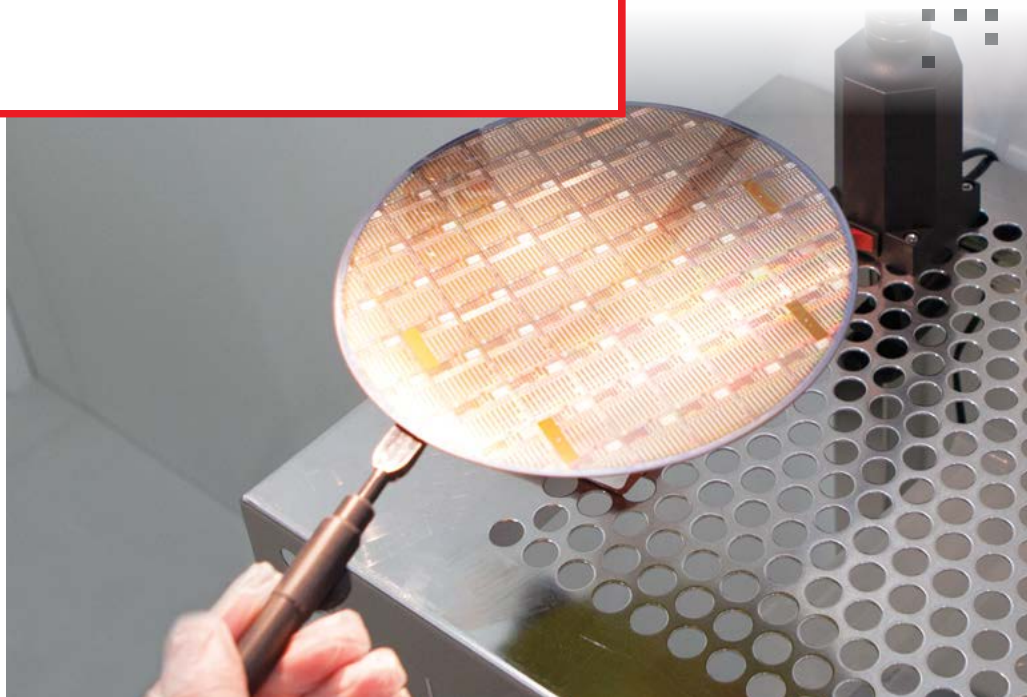


GaN POWER

Energy-efficient power electronics
with Gallium Nitride transistors



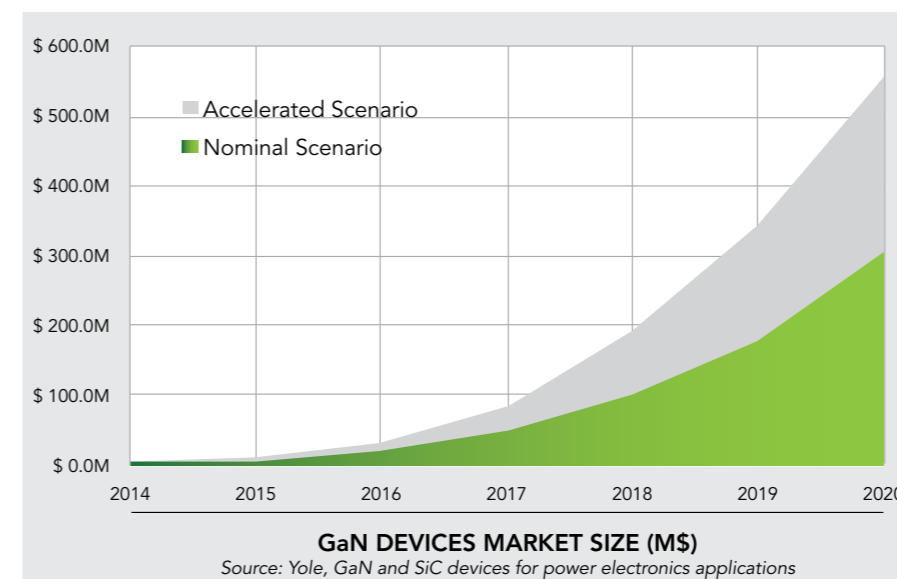
Leti GaN devices for next-era power-electronics applications

Leti is a technology research institute at CEA Tech. It has been involved in GaN/Si technology development since 2007, starting with the development of the material—a key in GaN-on-silicon device performance and cost.

CEA develops epitaxial GaN on 200mm silicon wafers and achieved state-of-the art electrical performance in 2015.

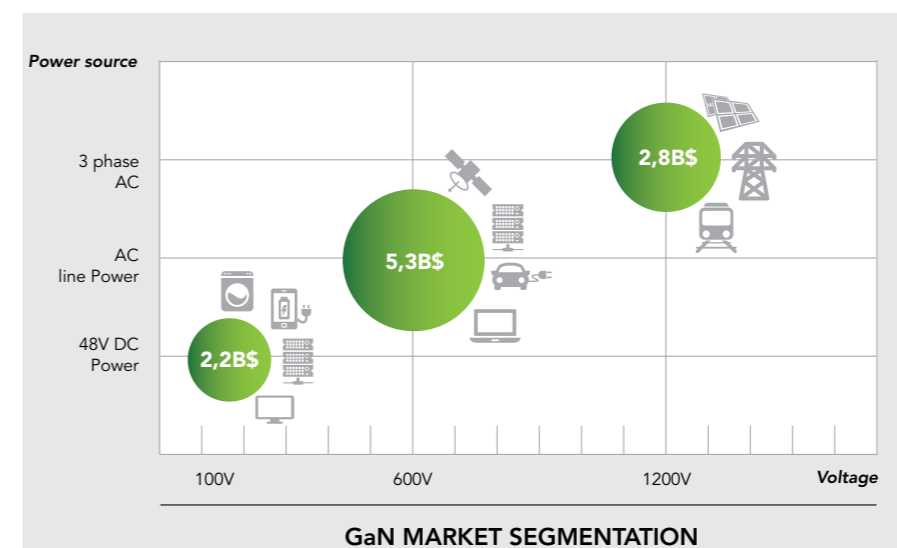
Leti is already involved with many industrial end users to develop new integrated systems with GaN inside. These mainly are for EV, in which GaN/Si devices are well adapted for DC-DC converters to improve power density for a more compact converter, increasing the final system efficiency.

A MARKET IN GROWTH



The GaN devices market for power-electronics applications will explode in 2016, reaching US\$303 million in 2020, according to Yole Développement (GaN and SiC devices for power electronics applications - July 2015). But growth could accelerate in 2017. In this case, the market's size will reach 1.8X that of the nominal scenario by 2020.

A LARGE RANGE OF APPLICATIONS



The current GaN devices market is mainly dominated by devices <200V. 600V devices are expected to take off and keep growing. While SiC is used for high-voltage applications, GaN is mainly used for low voltage. The 600-900V range will be the battlefield.

WHY GaN?

THANKS TO ITS PERFORMANCE, GaN WILL IMPROVE CONVERTER POWER DENSITY AT LOW COST

FOR ITS PERFORMANCE

GaN devices offer five key characteristics:

- high dielectric strength
- high operating temperature
- high current density
- high speed switching
- low on-resistance

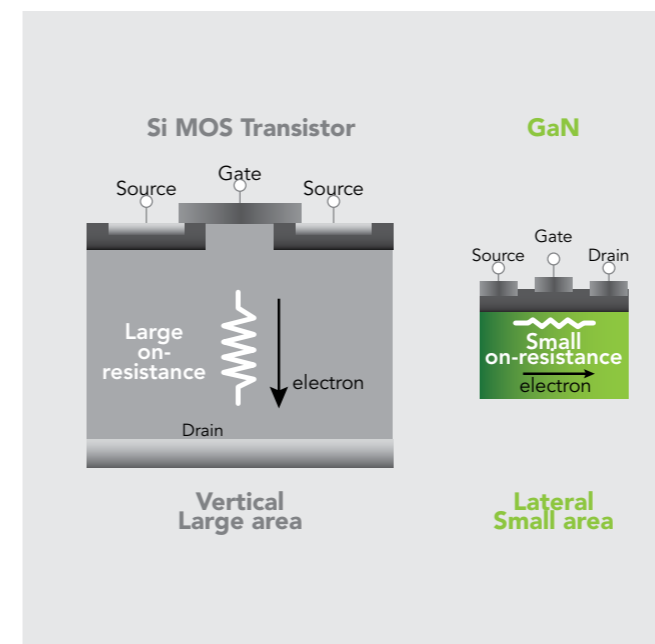
The special features of GaN such as high voltage potential, ease of miniaturization and high-speed switching, enable GaN to achieve high breakdown voltage and low conduction resistance.

The high breakdown voltage is achieved because GaN has a wide band gap property.

The low conduction resistance is achieved due to the high 2D electron gas mobility and density.



+ Best performance vs. silicon (equivalent as SiC)



FOR MORE EFFICIENT POWER CONVERTER

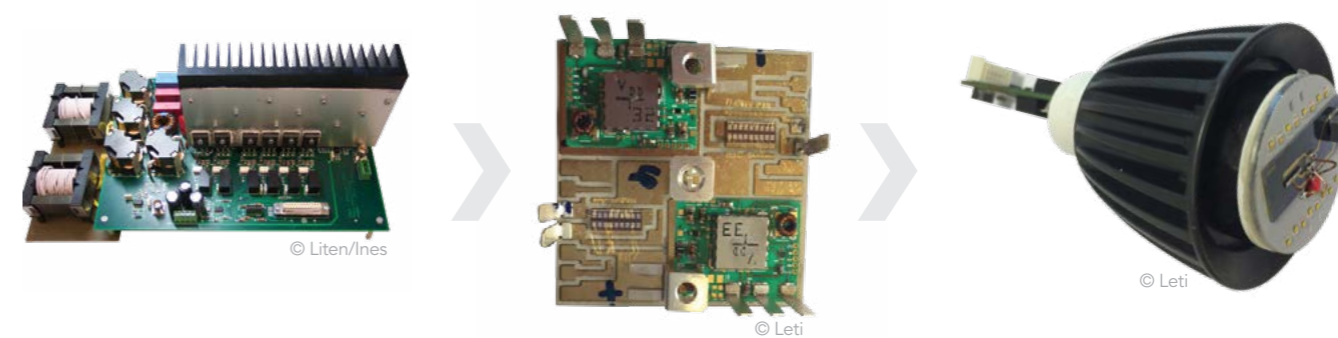
Easier monolithic integration capability

- More "clever" device with new integrated functions: temperature sensor, pre-driver, short circuit protection...
- Bidirectional switch
- High capabilities component
- Very low Ron.S
- Very high speed commutation switching
- Bidirectional monolithic component adapted to 4-quadrant power conversion

+ Smaller device with more integrated function

FOR SYSTEM BREAK INNOVATION

Smaller, more integrated and more efficient.



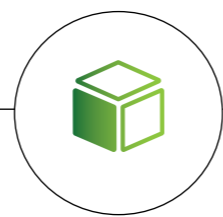
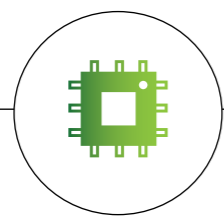
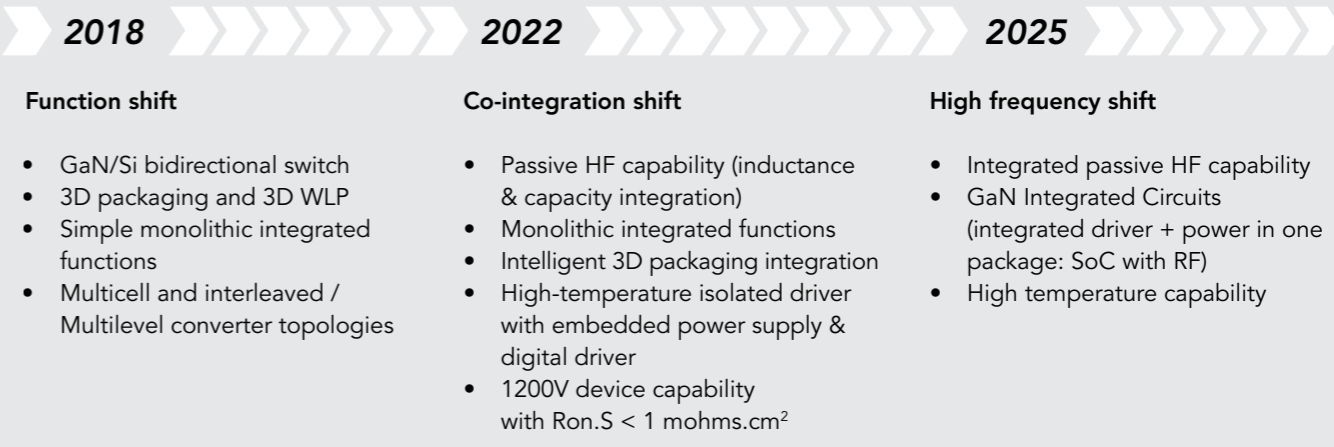
+ Best performance vs. silicon, cheaper than silicon and SiC solution

GaN transistors enable the compact design of LED

WHY LETI?

LETI'S VALUE PROPOSITION IS A COMPLETE CHAIN FROM DESIGN TO SYSTEM INTEGRATION AND OPTIMIZATION OF CONVERTER

WHAT NEXT? FROM DISCRETE... TO IC



COMPONENT

- 200mm CMOS compatible GaN/Si technology
- 200mm GaN/Si epitaxy with low leakage at 600V
- 600V N.ON and N.OFF devices
- Bidirectional GaN/Si Device

+ Multi approaches GaN technologies:

- Low gate leakage device architecture
- Low R_{on} capability for 600V ($R_{on.S} < 1 \text{ mohms.cm}^2$)
- High positive threshold voltage for N.OFF devices
- MOS HEMT devices

PACKAGING

+ 2 technology approach:

Optimized module for high current capability (KW segment):

- Low inductance integrated power module
- Integrated driver (SIP)
- Capacity integration near active transistors

Disruptive 3D packaging integration for more performance at high frequency (W segment):

- Pillar and bump connection technology
- Silicon active interposer
- TSV technology
- 3D wafer level packaging with copper leadframe
- Fan out wafer level packaging

CHARACTERIZATION & INDUSTRIAL TESTS

Specific electrical characterization:

- Current collapse (R_{on_dyn}) & V_t shift analysis
- Dynamic test: clamping inductive switching, gate charge
- Full static device characterization

Technological reliability test and failure analysis:

- Gate oxide integrity, TDDB at high voltage, HTRB, C(V)...
- Emission microscopy, DLTS, full physical characterization on a dedicated platform



SYSTEM INTEGRATION

Innovation for a more compact, efficient and low-cost converter:

- New high-frequency system design architecture to reduce passive size (resonant topology, matrix converter...)
- Better thermal management
- New high-temperature isolated driver with embedded power supply capability
- Monolithic commuted cell integration (capacity + half bridge)



ABOUT LETI

Leti is a technology research institute at CEA Tech and a recognized global leader in miniaturization technologies enabling smart, energy-efficient and secure solutions. Committed to innovation, its teams create differentiating solutions for Leti's industrial partners.

By pioneering new technologies, Leti enables innovative applicative solutions that ensure competitiveness in a wide range of markets. Leti tackles critical, current global issues such as the future of industry, clean and safe energies, health and wellness, safety & security...

Leti's multidisciplinary teams deliver solid micro and nano technologies expertise, leveraging world-class pre-industrialization facilities.

For 50 years, the institute has been building long-term relationships with its industrial partners providing tailor-made solutions and a clear intellectual property policy.

Leti, technology research institute

Commissariat à l'énergie atomique et aux énergies alternatives

Minatéc Campus | 17 rue des Martyrs | 38054 Grenoble Cedex 9 | France

www.leti.fr

